L Number	Hits	Search Text	DB	Time stamp
1	77641	356/\$.ccls.	USPAT;	2004/03/30
			US-PGPUB;	08:14
			EPO; JPO;	
			DERWENT; IBM TDB	
2	О .	356/\$.ccls. and dielectric adj3 viod	USPAT;	2004/03/30
	1-	•	US-PGPUB;	08:14
			EPO; JPO;	
			DERWENT; IBM TDB	
3	1	356/\$.ccls. and dielectric adj3 void	USPAT;	2004/03/30
		•	US-PGPUB;	08:14
			EPO; JPO;	
			DERWENT; IBM TDB	
4	16	356/\$.ccls. and layer adj3 void	USPAT;	2004/03/30
			US-PGPUB;	07:59
			EPO; JPO;	
			DERWENT; IBM TDB	
5	4759	356/237.1-237.5.ccls.	USPAT;	2004/03/30
			US-PGPUB;	07:59
			EPO; JPO;	
			DERWENT; IBM TDB	
6	1	356/237.1-237.5.ccls. and layer adj3 void	USPAT;	2004/03/30
	_		US-PGPUB;	08:00
			EPO; JPO;	
			DERWENT; IBM TDB	
7	153	356/237.1-237.5.ccls. and void	USPAT;	2004/03/30
			US-PGPUB;	08:15
			EPO; JPO;	
			DERWENT; IBM TDB	,
8	76	(356/237.1-237.5.ccls. and void) and	USPAT;	2004/03/30
		layer	US-PGPUB;	08:15
			EPO; JPO; DERWENT;	
			IBM TDB	
9	24	((356/237.1-237.5.cclsand_void)_and	USPĀT; — -	-2004/-03/-30
		layer) and dielectric	US-PGPUB;	08:16
			EPO; JPO; DERWENT;	
			IBM TDB	
10	104682	250/\$.ccls.	USPAT;	2004/03/30
			US-PGPUB; EPO; JPO;	08:14
			DERWENT;	
			IBM_TDB	
11	0	250/\$.ccls. and dielectric adj3 viod	USPAT;	2004/03/30
			US-PGPUB; EPO; JPO;	08:14
			DERWENT;	
			IBM_TDB	
12	6	250/\$.ccls. and dielectric adj3 void	USPAT;	2004/03/30 08:15
			US-PGPUB; EPO; JPO;	00:13
			DERWENT;	
]			IBM_TDB	0004/00/00
13	1520	250/\$.ccls. and void	USPAT; US-PGPUB;	2004/03/30 08:15
			EPO; JPO;	*****
			DERWENT;	
		(050/0 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	IBM_TDB	2004/02/20
14	863	(250/\$.ccls. and void) and layer	USPAT; US-PGPUB;	2004/03/30 08:15
			EPO; JPO;	00.13
			DERWENT;	
			IBM TDB	

15	250	((250/\$.ccls. and void) and layer) and	USPAT;	2004/03/30
		dielectric	US-PGPUB;	08:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	745674	processor	USPAT;	2004/03/30
			US-PGPUB;	08:16
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	58	(((250/\$.ccls. and void) and layer) and	USPAT;	2004/03/30
		dielectric) and processor	US-PGPUB;	08:17
			EPO; JPO;	
			DERWENT;	
	001		IBM_TDB	
18	221		USPAT;	2004/03/30
		dielectric) and (wafer or substrate)	US-PGPUB;	08:17
			EPO; JPO;	
			DERWENT;	
10		////250/6 mmlm =================================	IBM_TDB	2004/02/20
19	52		USPAT;	2004/03/30
		dielectric) and (wafer or substrate))	US-PGPUB;	08:17
		and processor	EPO; JPO;	
			DERWENT;	
	_	/#C134003#\ DN	IBM_TDB	2004/02/24
_	2	("6134002").PN.	USPAT;	2004/03/24
			US-PGPUB;	14:50
			EPO; JPO; DERWENT;	
			· ·	
	77564	356/\$.CCLS.	<pre>IBM_TDB USPAT;</pre>	2004/03/24
-	//364	356/\$.0015.	US-PGPUB;	15:48
			EPO; JPO;	12:40
			DERWENT;	
			IBM TDB	
l _	935	((356/\$).CCLS.) and ((wafer or substrate)	USPAT;	2004/03/24
	955	adj3 (tilt or angle))	US-PGPUB;	15:48
	1	days (crit or angre)	EPO; JPO;	10.10
			DERWENT;	
			IBM TDB	i i
_	2	("6556290").PN.	USPAT;	2004/03/24
[,	US-PGPUB;	14:35
i			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
-	0	(356/\$.ccls. and dielectric adj3 void)	USPAT;	2004/03/24
ĺ		and ((beam adj2 splitter) or	US-PGPUB;	15:06
İ		(beamsplitter))	EPO; JPO;	
İ			DERWENT;	
ĺ			IBM_TDB	
-	0		USPAT;	2004/03/24
İ		reflected	US-PGPUB;	14:46
İ			EPO; JPO;	
İ			DERWENT;	
ĺ		1256/4 3 1 1 2 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	2004/02/04
-	0		USPAT;	2004/03/24
ĺ		and ((wafer or substrate) adj3 (tilt))	US-PGPUB;	15:06
İ			EPO; JPO;	
İ			DERWENT;	
l _	0	(356/237.1-237.5.ccls. and layer adj3	IBM_TDB USPAT;	2004/03/24
-		void) and ((beam adj2 splitter) or	US-PGPUB;	15:21
		(beamsplitter))	EPO; JPO;	17.21
İ		(neamphireel)	DERWENT;	
			IBM TDB	
_	0	(356/\$.ccls. and dielectric adj3 void)	USPAT;	2004/03/24
		and 356/138-155.ccls.	US-PGPUB;	15:22
1			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
		A		